## 

VARO SEMICONDUCTOR, INC., P.O. BOX 40676 1000 NORTH SHILOH, GARLAND, TEXAS 75040 (214) 271-8511 TWX 910-860-5178

DLS100

## 60 Amp Center Tapped Schottky Barrier Rectifiers

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50 Volt and 60 Volt V<sub>RRM</sub> 30 Amps Per Leg 175°С Operating Junction Temperature Low Forward Voltage Drop Very Fast Recovery

Standard TO3 Package



MAXIMUM RATINGS (At T,=25°C unless otherwise noted)	SYMBOL	VSK231	VSK232	Units
Peak Repetitive Reverse Voltage	V <sub>BBM</sub>	60	50	Volts
Working Peak Reverse Voltage	V <sub>RWM</sub>	50	40	Volts
Peak Rectified Forward Current (# 50% Duty Cycle	I <sub>F</sub>	60		Amps
Peak Surge Current (non-rep), 1/2 cycle, 60Hz	I	600		Amps
Operating Junction Temperature	T	- 65 to + 175		°C
Storage Temperature	T <sub>SIG</sub>	- 65 to + 175		°C
Thermal Resistance, Junction to Case	R <sub>ejc</sub>	1.4		°C/W

Electrical Characteristics (At $T_{,} = 25^{\circ}$ C unless otherwise noted)	SYMBOL	VSK 231	VSK 232	UNITS
Maximum Instantaneous Forward Voltage Drop per diode $I_{F} = 30 \text{ Amps}$ $I_{F} = 60 \text{ Amps}$	V <sub>F</sub>	25°C 0.74 0.92	175° C 0.6 0.82	Volts
Maximum Instantaneous Reverse Current per diode $I_{F} = 25^{\circ}C$ $I_{F} = 125^{\circ}C$ $I_{F} = 150^{\circ}C$	I <sub>R</sub>	10 25 50		mA
Junction Capacitance $V_{_{\rm R}} = 5V$	C	2000		pF
Typical Reverse Recovery Time $I_F = I_R = 1A, T_c = \frac{125^{\circ}C}{Recovery}$	t <sub>r</sub>	50		n-sec
Rate of Change (PIV vs Time) $V_{p} = max$	dv/dt	2000		V/µs
Maximum Repetitive Peak Reverse Current 20 $\mu$ sec pulse f = 2KHz	IRM		4	Amps



LTR.	INCHES	MILLIMETERS
A	.72 Dia	18.29
В	.323342	8.20 - 8.69
С	.40 Min	10.16
D	.038 — .043 Dia	.97 — 1.09
Е	1.180 1,194	29.97 30.33
F	.665 — .675	16.89 — 17.15
G	.426 — .440	10.82 — 11.18
н	.525R Max	13.34
	.151 — .161 Dia	3.84 - 4.09



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